TOSHIBA Transistor Silicon-Germanium NPN Epitaxial Planar Type

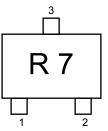
MT3S113TU

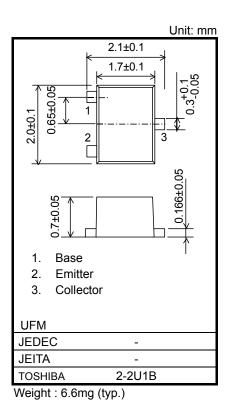
VHF-UHF Band Low-Noise, Low-Distortion Amplifier Applications

FEATURES

- Low Noise Figure:NF=1.15dB(Typ.) (@ f=1GHz)
- High Gain:|S21e|²=12.5dB(Typ.) (@ f=1GHz)

Marking





Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-emitter voltage	V _{CES}	13	V
Collector-emitter voltage	V _{CEO}	5.3	V
Emitter-base voltage	V _{EBO}	0.6	V
Collector-current	Ι _C	100	mA
Base-current	Ι _Β	10	mA
Collector power dissipation	P _C (Note1)	900	mW
Junction temperature	Тј	150	°C
Storage temperature range	T _{stg}	–55 to 150	°C

Note1:The device is mounted on a ceramic board (25.4 mm x 25.4 mm x 0.8 mm (t))

Note2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	V _{CE} =5V,I _C =50mA	9	11.2	_	GHz
Insertion gain	S21e ² (1)	V _{CE} =5V,I _C =50mA,f=500MHz	_	18	_	dB
	S21e ² (2)	V _{CE} =5V,I _C =50mA,f=1GHz	10.5	12.5	_	dB
Noise figure -	NF(1)	V _{CE} =5V,I _C =50mA,f=500MHz	_	0.88	_	dB
	NF(2)	V _{CE} =5V,I _C =50mA,f=1GHz	_	1.15	1.45	dB
3 rd order intermodulation distortion output intercept point	OIP3	V _{CE} =5V,I _C =50mA,f=500MHz, ⊿f=1MHz	30.5	34.8		dBmW

Electrical Characteristics (Ta = 25°C)

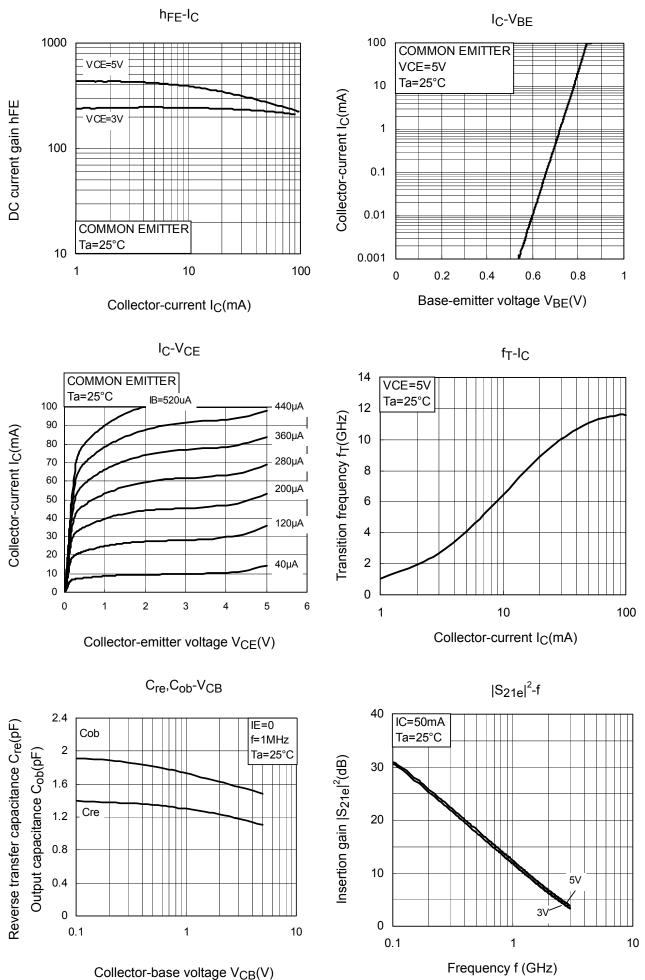
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} =5V,I _E =0	_	_	0.1	μA
DC current gain	h _{FE}	V _{CE} =5V,I _C =30mA	200	_	400	_
Output capacitance	C _{ob}	V _{CB} =5V,I _E =0, f=1MHz	_	1.49	_	pF
Reverse transfer capacitance	C _{re}	V _{CB} =5V,I _E =0, f=1MHz (Note3)		0.94	1.25	pF

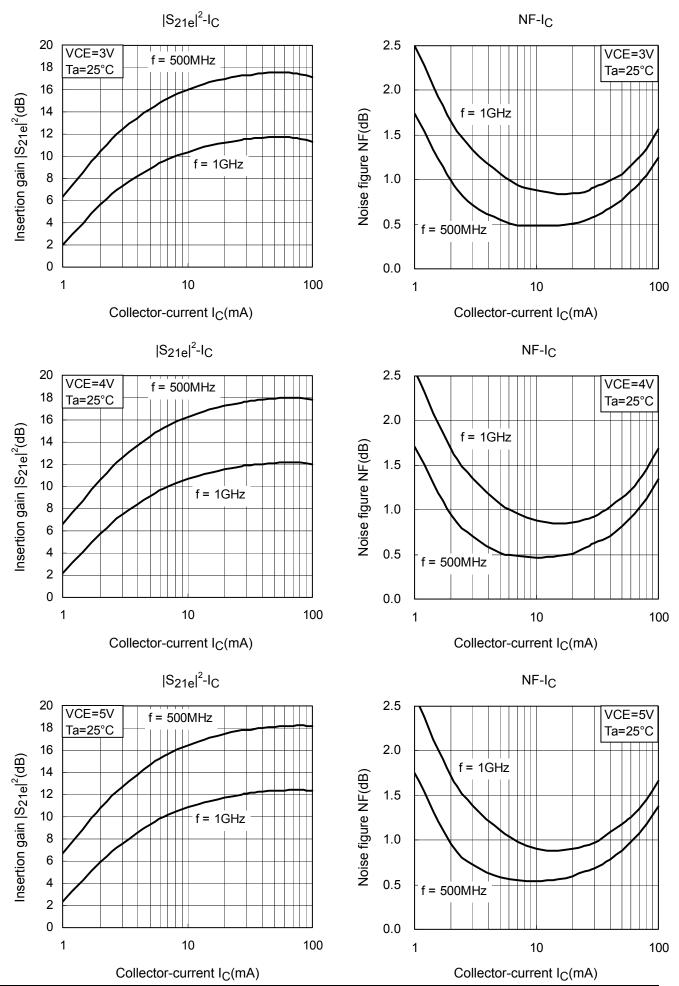
Note $3:C_{re}$ is measured using a 3-terminal method with capacitance bridge

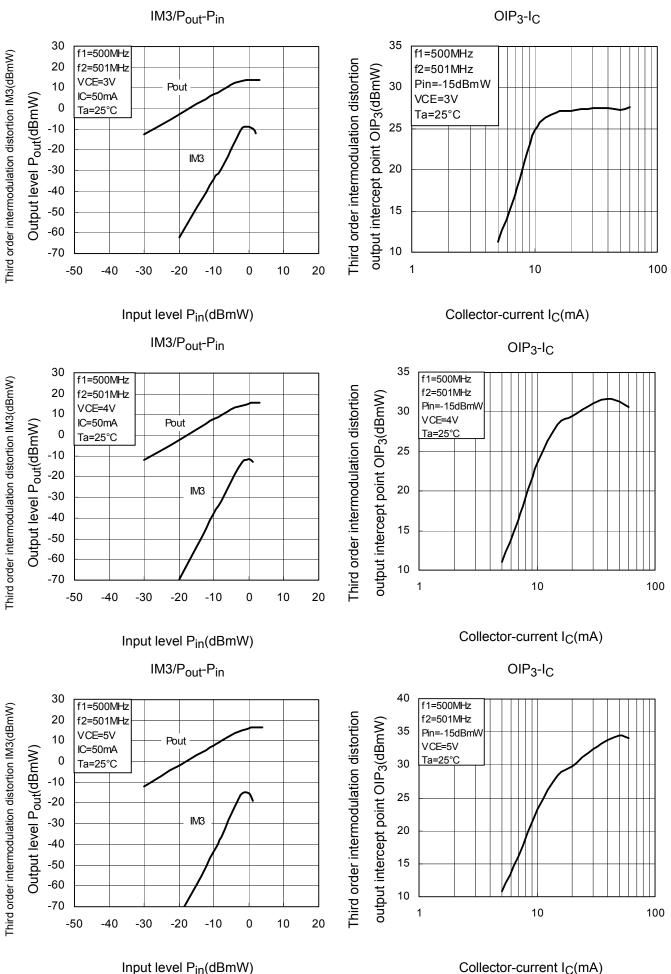
Caution:

This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of f_T =60GHz class is used for this product.

Please make enough tool and equipment earthed when you handle.

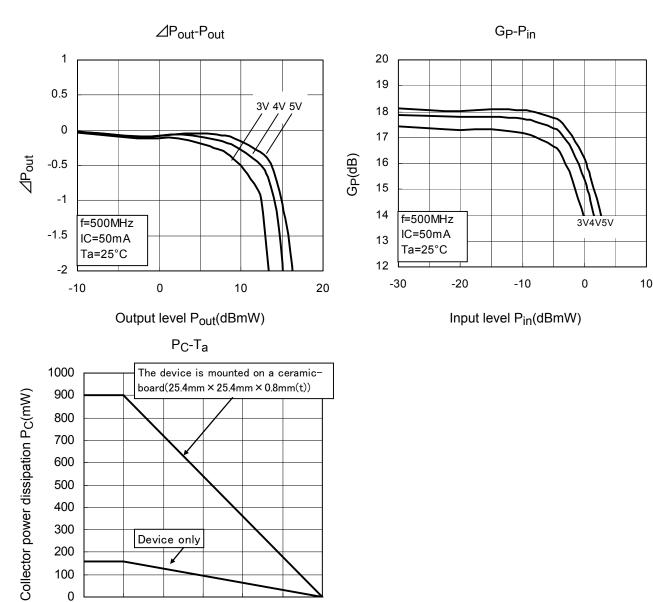






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Ambient temperature Ta(°C)



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